

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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Title of Invention

HIGH PRESSURE PROCESSING CHAMBER FOR
SEMICONDUCTOR SUBSTRATE

Application Number : 09/912844



Confirmation Number: 5915

First Named Applicant: Maximilian Biberger

Attorney Docket Number:

Art Unit:

Examiner:

Search string: (3681171 or 4827867 or 5009738 or 6221781 or 6306564 or 6497239 or 20030005948).pn

Certification: This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	3681171	1972-08-01	Toku Hojo et al.			
	2	4827867	1989-05-09	Takei et al.			
	3	5009738	1991-04-23	Gruenwald et al.			
	4	6221781	2001-04-24	Siefering et al.	B1		
	5	6306564	2001-10-23	Mullee	B1		
	6	6497239	2002-12-24	Farmer et al.	B2		

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20030005948	2003-01-09	Matsuno et al.	A1		

Signature

Examiner Name	Date